S. Departmer	nt of Com	rece, Patent and Trademark Office	Atty Docket No.	Serial No.		
		& IRAD	NS-4971 US	09/903,059		
INFOR	MATIO	N DISCLOSURE STATEMENT BY APPLICANT	Applicant			
(Use several sheets if necessary)			Bulucea, Constantin	Bulucea, Constantin		
			Filing Date	Group		
			July 10, 2001	2814		
		OTHER ART (Including Author, Title, Dat	e, Pertinent Pages, Etc.)			
OF	AA	Andreani, et al., "A 1.8-GHZ CMOS VCO Tuned by an Accumulation-Mode MOS Varactor," IEEE Intl. Symposium on Circuits and Systems, 28 – 31 May 2000, pp. I-315 – I - 318.				
OF	AB	Grove, Physics and Technology of Semiconductor Devices (John Wiley & Sons), 1967, pp. 263 – 305.				
DF.	AC	Grove, et al., "Effect of Surface Fields on the Breakdown Voltage of Planar Silicon <i>p-n</i> Junction," <u>IEEE Trans. Electron Devices</u> , Vol. ED-14,1967, pp. 157 – 162.				
OF	AD	Grove, et al., "Surface Effects on <i>p-n</i> Junctions: Characteristics of Surface Space-Charge Regions Under Non-Equilibrium Conditions," <u>Solid-State Electronics</u> , Vol. 9, 1966, pp. 783 - 806.				
OF	AE	Kral, et al., "RF-CMOS Oscillators with Switched Tuning," <u>Procs. IEEE Custom Integrated Circuits Conference</u> , 1998, pp. 555 – 558.				
0F	AF	Lee, <u>The Design of CMOS Radio-Frequency Integrated Circuits</u> (Cambridge Univ. Press), 1998, pp. 37 – 41 and 504 – 514.				
OF	AG	McMahon, et al., "Voltage-Sensitive Semiconductor Capacitors," 1958 IRE Wescon Conf. Rec., Part 3, 19 – 22 August 1958, pp. 72 – 82.				
OF	АН	Moll, "Variable Capacitance With Large Capacity Change", <u>IRE Wescon Conf. Rec.</u> , Vol. 3, 1959, pp. 3 - 36.				
0 F	AI	Ng, Complete Guide to Semiconductor Deices (McGraw Hill), 1995, pp. 11 - 22.				
0 F	AJ	Razavi, Design of Analog CMOS Integrated Circuits (McGraw Hill), 2001, pp. 495 – 525.				
OF	AK	Rusu et al., "Deep-Depletion Breakdown Voltage of Silicon-Dioxide/Silicon MOS Capacitors", <u>IEEE Trans. Elec. Devs.</u> , March 1979, pp. 201 - 205.				
0 F	AL	Rusu et al., "Reversible Breakdown Voltage Collapse in Silicon Gate-Controlled Diodes" Solid-State Electronics, Vol. 23, 1980, pp. 473 - 480.				
<b>O</b> F	AM	Svelto, et al., "A Three Terminal Varactor for RF IC's in Standard CMOS Technology," <u>IEEE Transactions on Electron Devices</u> , Vol. 47, 2000, pp. 893 – 895.				
Examiner (	77	Date Considered 8/2	3/02			

.s. Departi	Department of Commerce, Patent and Trademark Office		Atty Docket No.	Serial No.			
			NS-4971 US	09/903,059			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)			Applicant				
			Bulucea, Constantin				
·			Filing Date	Group			
	·		July 10, 2001	2814			
		OTHER ART (Including Author, Title, Date, Pe	ertinent Pages, Etc.)				
OF	AN	Warner, Jr., et al., <u>Transistors – Fundamentals for the Integrated-Circuit Engineer</u> (John Wiley & Sons) 1983, pp. 320 – 321.					
OF OF	AO	Wong et al., "A Wide Tuning Range Gated Varactor", <u>I</u> 779.	EEE J. Solid State Circs., Ma	y, 2000, pp. 773 –			
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xaminer 💋	2 /	hei Date Considered 8/23/0	7				
		f reference considered, whether or not citation is in conform					